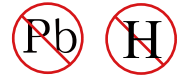
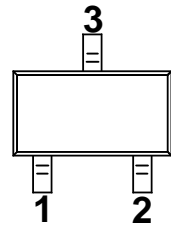




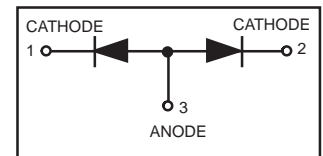
Dual Switching Diodes



SOT-323

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mA dc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA dc



THERMAL CHARACTERISTICS

Marking :A1

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	0.625	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate ⁽²⁾ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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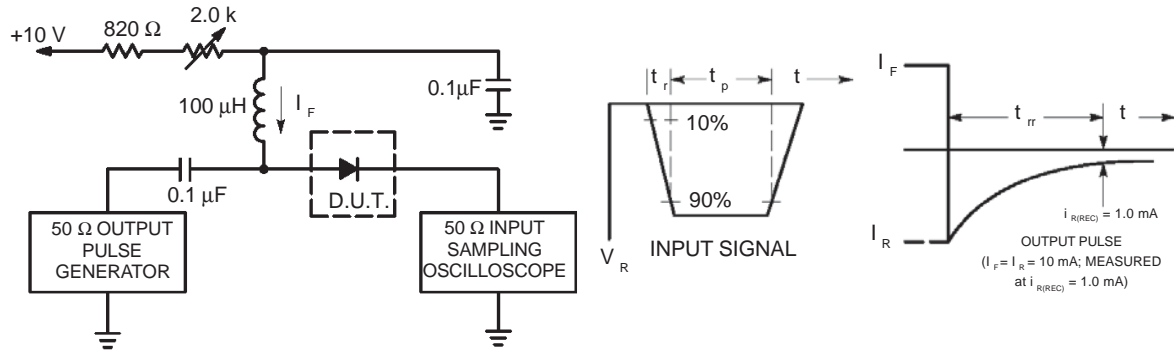
OFF CHARACTERISTICS

Reverse Breakdown Voltage ($I_{BR} = 100 \mu\text{A dc}$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ($V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$)	I_R	—	30	$\mu\text{A dc}$
($V_R = 70 \text{ Vdc}$)		—	2.5	
($V_R = 70 \text{ Vdc}, T_J = 150^\circ\text{C}$)		—	50	
Diode Capacitance ($V_R = 0, f = 1.0 \text{ MHz}$)	C_D	—	2.0	pF
Forward Voltage ($I_F = 1.0 \text{ mA dc}$)	V_F	—	715	mVdc
($I_F = 10 \text{ mA dc}$)		—	855	
($I_F = 60 \text{ mA dc}$)		—	1000	
($I_F = 150 \text{ mA dc}$)		—	1250	
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA dc}, R_L = 100 \Omega, I_{R(REC)} = 1.0 \text{ mA dc}$) (Figure 1)	t_{rr}	—	6.0	ns

1. FR-5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$ 2. Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.

DEVICE CHARACTERISTICS

BAW56W



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

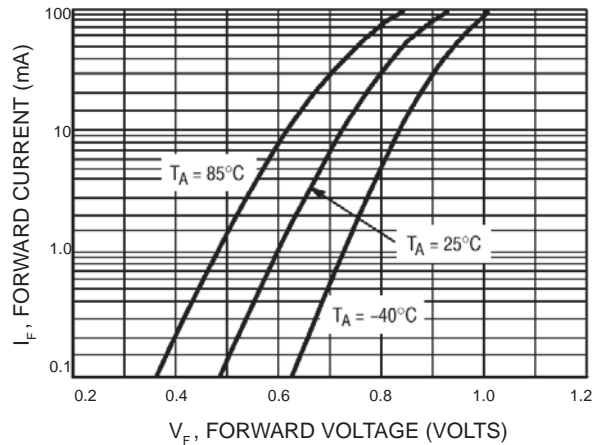


Figure 2. Forward Voltage

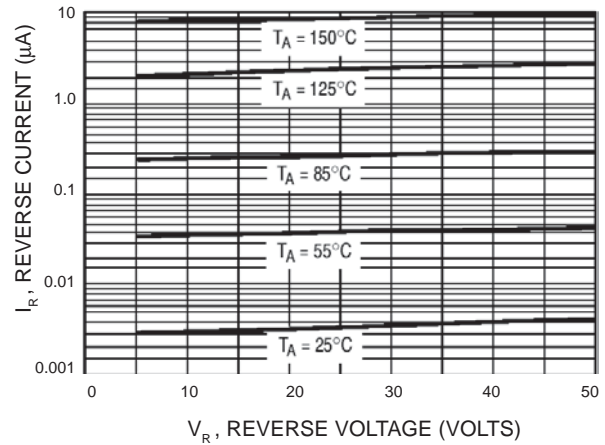


Figure 3. Leakage Current

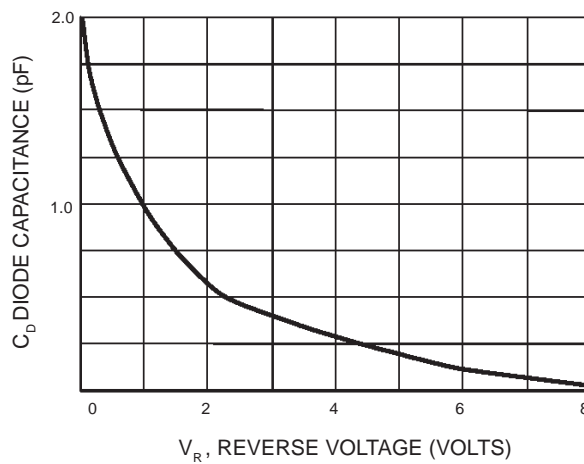
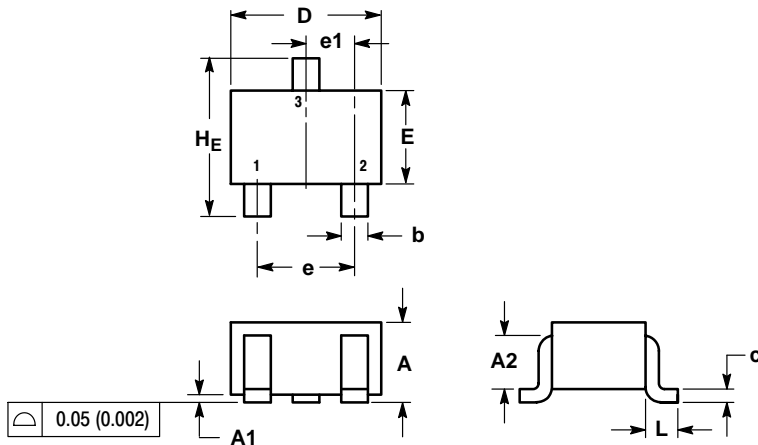


Figure 4. Capacitance

PACKAGE OUTLINE & DIMENSIONS

BAW56W

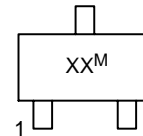
SOT-323



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
H _E	2.00	2.10	2.40	0.079	0.083	0.095

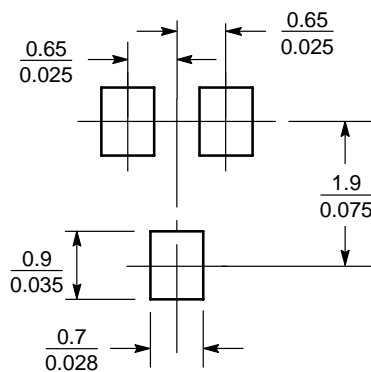
GENERIC MARKING DIAGRAM



XX = Specific Device Code
 M = Date Code
 ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)